

# ELECTROMAGNETIC DESIGN OF W-BAND CIRCUITS IN LTCC TECHNOLOGY

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## Summary

- Electromagnetic modelling and design of several millimetre wave components and circuits fabricated using **Low-Temperature Co-fired Ceramic (LTCC)** technology.
- The circuits include **embedded transmission lines** and **vertical transitions** designed to operate in the **W band**.



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## OUTLINE

- ❑ INTRODUCTION
- ❑ DESIGN AND TECHNOLOGICAL SETUP
- ❑ TRANSMISSION LINES AND VERTICAL TRANSITIONS
- ❑ **EXPERIMENTAL RESULTS**
- ❑ CONCLUSIONS

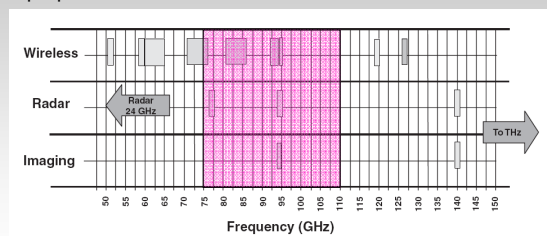


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## INTRODUCTION

Many millimeter-wave system applications such as **video transmission systems**, **broadband wireless**, **passive sensing** and **automotive radar** have been proposed in the last decade.



*The W band covers the 75 – 110 GHz frequency range*



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## INTRODUCTION

- ❑ Development of **compact** and **low cost** RF modules is necessary.
- ❑ **System-in/on-Package** (SiP/SoP) **approach** is widely regarded as an excellent means of realizing very compact multifunctional modules.
- ❑ A variety of technologies can be employed, including **Low-Temperature Co-fired Ceramic** (LTCC), **liquid crystal polymer** (LCP), organic and thin film on glass, etc.
- ❑ The **three-dimensional (3-D) integration** approach using multilayer **LTCC** technologies demonstrated a high level of compactness and mature multilayer fabrication capability (up to V band).



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## INTRODUCTION

- ❑ **LTCC technology** enables integration of **passive components** including antennas with **MMICs** in a single, cost-effective package.
- ❑ Passive structures, including transmission lines, can be placed at different layers, and three-dimensional integration enables miniaturization of modules.
- ❑ **LTCC** exhibits a **low dielectric loss, and conductor losses** are also low due to gold and silver conductors that can be used as metallization.
- ❑ The development of a **design library** of **basic circuits** for mm-wave frequency range is a essential.



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## DESIGN AND TECHNOLOGICAL SETUP

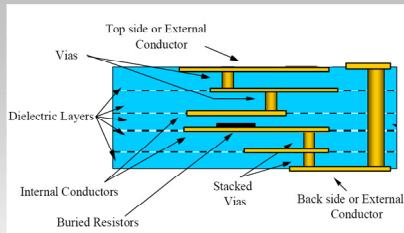
- ❑ Low-Temperature Co-fired Ceramic (LTCC) technologies:
  - high level of compactness and miniaturization
  - mature multilayer fabrication capability (up to 70 layers)
  - **three-dimensional (3-D) integration**
  - cost-effective package with integrated antennas
  - low dielectric loss, and conductor losses
  - passive structures placed on different layers
  - **Strip lines** and **Substrate Integrated Waveguides** (SIW) possible



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## DESIGN AND TECHNOLOGICAL SETUP



Cross section of the LTCC structure

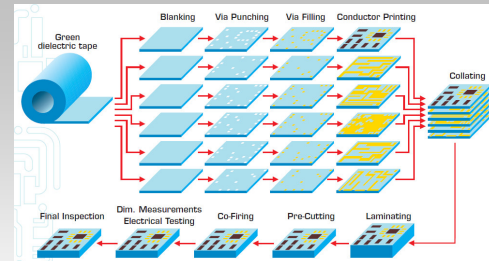
**Advantages:** low conductor and dielectric losses, good thermal conductivity, stability, hermeticity, low cost, air cavities and conducting vias.



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## DESIGN AND TECHNOLOGICAL SETUP



**Disadvantages:** fabrication tolerances at millimeter-wave region, high dielectric constant of the tape material (surface waves).



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## DESIGN AND TECHNOLOGICAL SETUP

❑ The test structures were **first** modeled and designed in frequency domains using the commercial **MoM** software package **Zeland IE3D**.

❑ In IE3D software the port definition and S parameter extraction is optimized for **current density distribution** and planar microwave circuits.

❑ The most accurate results are obtained for **in-plane differential ports** (like for CPW) and ports with **infinite ground extension**.



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## DESIGN AND TECHNOLOGICAL SETUP

❑ For **differential ports placed in different planes** (like those required for striplines with finite extensions for ground planes) the **IE3D** simulated results can be inaccurate for frequencies up to 100 GHz because of high order modes generation.

❑ A different commercial software package (**CST Microwave Studio**) was used to check the electromagnetic models and the designs.

❑ CST Microwave Studio uses **time domain** simulations and the port definition, S parameter extraction is optimized for **electric field distribution** (ideal for **waveguide port** and planar ports with multiple pins definition).



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### DESIGN AND TECHNOLOGICAL SETUP

□ The circuits were designed using the **Ferro A6-S** LTCC tape system with a fired tape **thickness of 100  $\mu\text{m}$** .

□ The diameter of all **vias is 100  $\mu\text{m}$**  and the minimum spacing between two adjacent vias is **250  $\mu\text{m}$**  (center to center).

- The electrical parameters:
- dielectric constant  $\epsilon_r = 5.9$
  - loss tangent 0.001 (@10 GHz)
  - silver paste conductivity  $\sigma = 3 \cdot 10^7 \text{ S/m}$ ,
  - conductor thickness  $t = 10 \mu\text{m}$ .

**The main restriction from the design rules are the minimum conductor widths and spacing of 100  $\mu\text{m}$ .**



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### DESIGN AND TECHNOLOGICAL SETUP

The designed **test circuits** for the **W band** operation are:

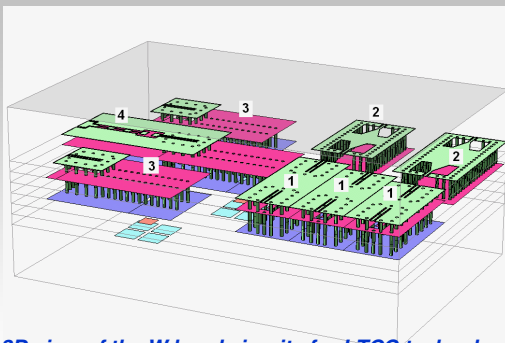
1. **CPW-stripline-CPW**; three different lengths for the stripline between the two transitions
2. **CPW-SIW-CPW**; two lengths for the SIW (**Substrate Integrated Waveguide**)
3. **Antenna element** integrated with CPW-stripline transition
4. **Antenna element** integrated with vertical transition and pads for mounting of a mm-wave Schottky diode.



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### DESIGN AND TECHNOLOGICAL SETUP



**3D view of the W band circuits for LTCC technology**



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## TRANSMISSION LINES AND VERTICAL TRANSITIONS

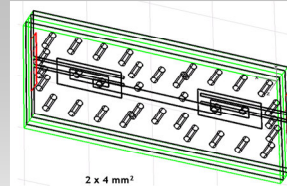
- At very high frequencies (up to 110 GHz) the modeling and design of the LTCC circuits is a challenge because the wavelength (**1235  $\mu\text{m}$  at 100 GHz**, including the tape dielectric permittivity) have the same order of magnitude with the vertical transitions dimensions and the dimensions of other circuit components.
- The **0D (lumped elements) and even 1D (transmission lines)** equivalent circuit modeling approach can no longer be used
- Full wave electromagnetic simulations** must be used in the design and optimization.



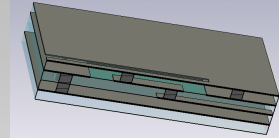
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## 1. CPW – stripline – CPW test structure



3D view of the two vertical transitions



Cross section of the CPW to SL vertical transition

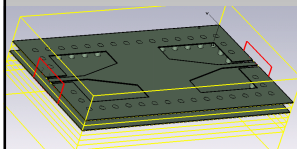


Type: PowerFlow (peak)  
Monitor: power (P=77) [1]  
Plane at: 0  
Material: 26  
Material: 26  
Frequency: 77

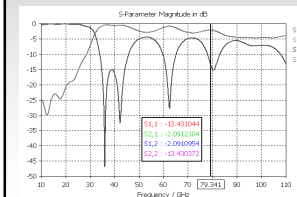
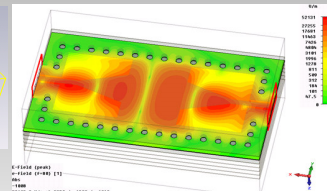
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## 2. CPW – SIW transition test structure



3D view of the two CPW to SIW transitions



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## EXPERIMENTAL RESULTS

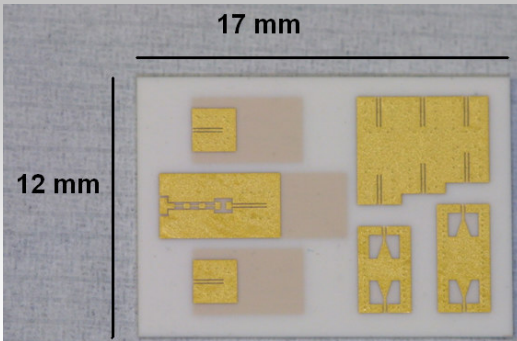
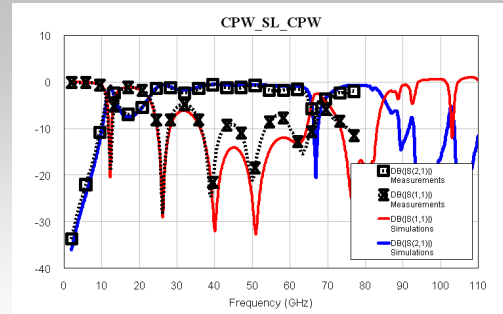


Photo of the fabricated LTCC test structures

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## EXPERIMENTAL RESULTS

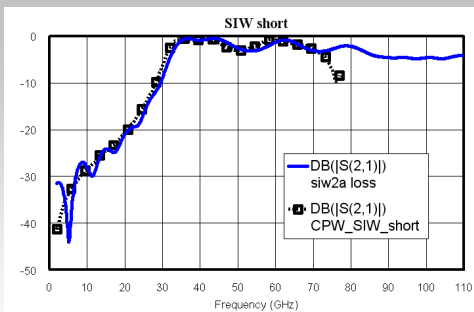


Simulated and measured S parameters for the two vertical transitions connected by an embedded stripline (long line)

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## EXPERIMENTAL RESULTS



Simulated and measured S parameters for the two CPW - SIW transitions connected by SIW (short line)

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## CONCLUSIONS

- Based on LTCC technology, embedded transmission lines and their transition to grounded CPW were designed.
- Test circuits were fabricated using the LTCC technology available at VTT, Finland.
- From measurements the LTCC material parameters can be extracted and the electromagnetic models can be refined.

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## ACKNOWLEDGMENT

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# Thank you



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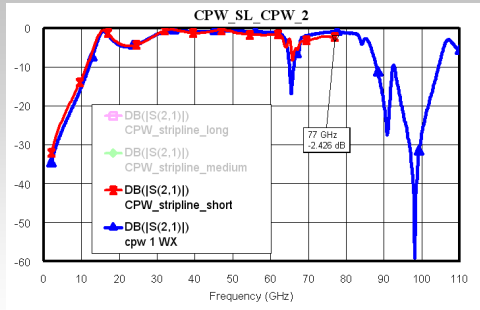
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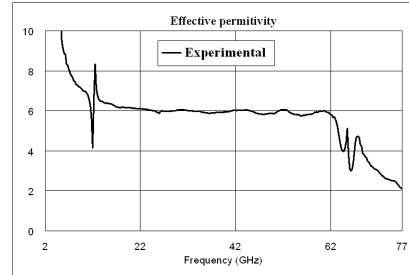
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$$\gamma = \frac{1}{\Delta L} \arg \left( \frac{S_{11}^B S_{22}^A + S_{11}^A S_{22}^B - \Delta_A - \Delta_B}{2 - S_{21}^B S_{12}^A} \right)$$

$$\Delta L = L_B - L_A$$

$$\Delta_A = S_{11}^A S_{22}^A - S_{12}^A S_{21}^A$$

$$\Delta_B = S_{11}^B S_{22}^B - S_{12}^B S_{21}^B$$



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